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INFORMATION DISCLOSURE STATEMENT BY APPLICANT										APPLICANT TORII et al.						
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For: Our New U.S. Patent Application. Our Ref: 7270 [SEMICONDUCTOR DEVICE AND ITS FABRICATION METHOD] (K. TORII; et al)

LIST OF THE PRIOR ART REFERENCES CITED IN THE SPECIFICATION

- 1. Japanese Laid-Open No.5-090606. (Cited on page 1, line 26)
- 2. Japanese Laid-Open No.2-288368. (Cited on page 2, line 11)
- 3. Japanese Laid-Open No.3-256358. (Cited on page 2, line 16)
- 4. Japanese Laid-Open No.7-014993. (Cited on page 2, line 24)
- 5. Japanese Laid-Open No.7-169854. (Cited on page 3, line 6)